24. (New) A method for depositing a tungsten silicide film comprising:

forming a tungsten silicide layer on a polysilicon layer, and

adding a phosphorus atom containing gas to a reactive gas at least in the initial stage that said tungsten silicide layer is formed.

25. (New) A method for preparing a gate electrode/wiring, which comprises:

depositing a tungsten silicide layer on a polysilicon layer,

depositing a silicon layer on said tungsten silicide layer,

forming a passivation film on the silicon layer, and

B' forming a silicon oxide film on a side wall of a gate electrode/wiring layer including said polysilicon layer and said tungsten silicide layer.

26. (New) A gate electrode/wiring structure comprising:

a polysilicon layer;

a tungsten silicide layer formed on said polysilicon layer;

a silicon layer formed on tungsten silicide layer; and

a passivation film on the silicon layer.

27. (New) A gate electrode/wiring structure comprising:

a polysilicon layer;

a tungsten silicide layer formed on said polysilicon layer; and

a silicon layer formed on said tungsten silicide layer,

wherein the tungsten silicide layer includes phosphorous atoms.